## RT1N430X SERIES

**(Transistor)** 

UNIT: mm

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

OUTLINE DRAWING

### **DESCRIPTION**

RT1N430X is a one chip transistor with built-in bias resistor, PNP type is RT1P430X.

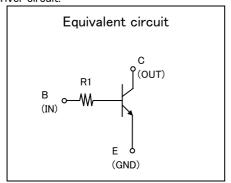
### **FEATURE**

•Built-in bias resistor (R1=4.7k $\Omega$ )

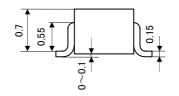
### **APPLICATION**

Inverted circuit, switching circuit, interface circuit.

driver circuit.



## 



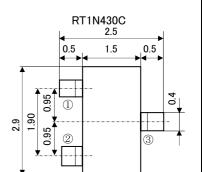
JEITA: — JEDEC: —

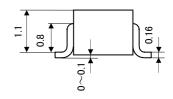
**Terminal Connector** 

1: Base

2: Emitter

3: Collector





JEITA: SC-59

JEDEC: Similar to TO-236

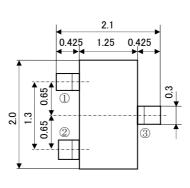
**Terminal Connector** 

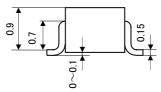
1:Base

2:Emitter

3: Collector

RT1N430M





JEITA:SC-70 JEDEC:—

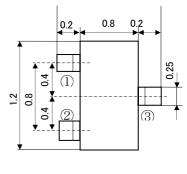
Terminal Connector

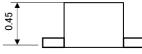
①:Base

2: Emitter

3: Collector

#### RT1N430T





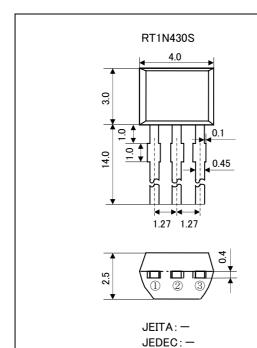
JEITA: — JEDEC: —

Terminal Connector

①:Base

2: Emitter

3: Collector



**Terminal Connector** 

(1): Emitter

3:Base

2: Collector

# RT1N430X SERIES

**(Transistor)** 

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

## MAXIMUM RATING (Ta=25°C)

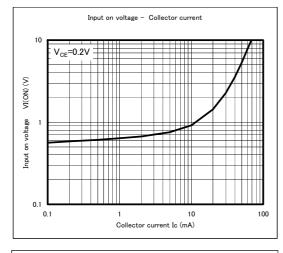
SYMBOL	PARAMETER	RATING					UNIT
		RT1N430T	RT1N430U	RT1N430M	RT1N430C	RT1N430S	UNIT
$V_{\text{CBO}}$	Collector to Base voltage	50					V
$V_{\sf EBO}$	Emitter to Base voltage	6					V
$V_{CEO}$	Collector to Emitter voltage	50					V
I c	Collector current	100					mA
I <sub>CM</sub>	Peak Collector current	200					mA
Pc	Collector dissipation(Ta=25°C)	125 (※ )	150	20	00	450	mW
Tj	Junction temperature	+125	+125 +150				°C
Tstg	Storage temperature	<b>-55∼+125 -55∼+150</b>				°C	

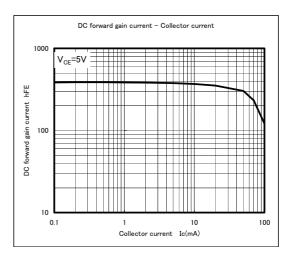
( $\mbox{\%}$  ) package mounted on 9mm × 19mm × 1mm glass-epoxy substrate.

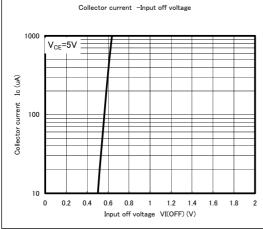
## ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	I <sub>C</sub> =100 μ A, R <sub>BE</sub> =∞	50			٧
I <sub>CBO</sub>	Collector cut off current	$V_{CB}$ =50V, $I_{E}$ =0			0.1	μΑ
$h_{FE}$	DC forward current gain	$V_{CE}$ =5V, I $_{C}$ =1mA	100			ı
$V_{CE(sat)}$	C to E saturation voltage	$I_{C}$ =10mA, $I_{B}$ =0.5mA		0.1	0.3	٧
R <sub>1</sub>	Input resistance		3.3	4.7	6.1	kΩ
$f_{T}$	Gain band width product	$V_{CE}=6V$ , $I_{E}=-10mA$		200		MHz

### TYPICAL CHARACTERISTICS









Marketing division, Marketing planning department 6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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